

45. The light emitting device of Claim 35, further comprising a first contact and a second contact electrically coupled to apply a voltage across said active region; said first contact and said second contact disposed on a same side of said stack.

47/46. The light emitting device of Claim 36, further comprising a first contact and a second contact electrically coupled to apply a voltage across said active region; said first contact and said second contact disposed on a same side of said stack.

47. A light emitting device having a stack of layers including semiconductor layers comprising an active region, said device comprising:
a lens bonded to said stack; and
a first contact and a second contact electrically coupled to apply a voltage across said active region;
wherein said stack of layers comprises at least one III-Phosphide semiconductor layer and said first contact and said second contact are disposed on a same side of said stack.

48. The light emitting device of Claim 47 wherein said lens comprises GaP.

49. A light emitting device having a stack of layers including semiconductor layers comprising an active region, said device comprising:
a lens bonded to said stack; and
a first contact and a second contact electrically coupled to apply a voltage across said active region;
wherein said stack of layers comprises at least one III-Nitride semiconductor layer and said first contact and said second contact are disposed on a same side of said stack.

50. The light emitting device of Claim 49 wherein said lens comprises ZnS.

REMARKS

New Claims 43-50 are supported, for example, in the specification at page 17 lines 10-28 and by Figures 6 and 7. No new matter has been added. If the Examiner would like to

737578 v1 / PF-OA [Rev. 000913]